#### IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): FUKUDA et al. Atty. Dkt.: 01-493

Serial No.: Unknown Group Art Unit:

Filed: Concurrently herewith Examiner:

Title: SEMICONDUCTOR EQUIPMENT

Commissioner for Patents Arlington, VA 22202

Date: October 21, 2003

## INFORMATION DISCLOSURE STATEMENT

Sir:

Pursuant to 37 C.F.R. §1.56, the reference(s) listed on the attached Form PTO-1449 is/are submitted for consideration by the Examiner without any admission that it/they constitute(s) statutory prior art, or without any admission that it/they contain(s) subject matter that anticipates the invention or renders the invention obvious to a person of ordinary skill in the art.

The Examiner is requested to initial the attached PTO Form-1449 and to return a copy of same to the undersigned attorney as proof that the listed reference(s) has/have been considered and made of record.

Respectfully submitted,

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# \* PATENT APPLICATION

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FORM PTO-1449	ATTY. DKT NO.	01-493	SER. NO.	
	APPLICANT	FUKUDA et al.		
	FILING DATE	October 21, 2003	GROUP	

#### REFERENCE DESIGNATION

## **U.S. PATENT DOCUMENTS**

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS
	4,636,825	Jan. 13, 1987	Baynes		
	4,948,754	Aug. 14, 1990	Kondo et al.		
	5,192,989	Mar. 9, 1993	Matsushita et al.		
	5,412,239	May 2, 1995	Williams		-
	5,672,894	Sep. 30. 1997	Maeda et al.		

## FOREIGN PATENT DOCUMENTS

TRANSLATION

DOCUMENT NUMBER	DATE	COUNTRY	NAME	CLASS	SUB CLASS	YES	NO
JP-A-H07-263665 (Discussed in page 1 of the spec.)	10/13/95	JAPAN				X (Abstract)	
JP-A-H03-239369	10/24/91	JAPAN				X (Abstract)	

<sup>\*</sup> Full English text of the JP Document will be available in machine-translated form from JP (Japanese Patent Office) English language web site at http://www1.ipdl.jpo.go.jp/PA1/cgi-bin/PA1INDEX.

## OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

1, 5/22/2000, pp.1-6
tional Rectifier", IRF6150, PD-93943, pp. 1-3
chofield et al., "FlipFET™ MOSFET Design for High Volume SMT ly", International Rectifier, pp.1-6
DATE CONSIDERED

Rev. 10/94 (Form 3.05)